

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A gap fill material forming composition ~~characterized in that wherein~~ the composition is used in manufacture of semiconductor device by a method comprising coating a photoresist on a substrate having a hole with aspect ratio shown in height/diameter of 1 or more, and transferring an image to the substrate by use of lithography process, ~~and that the composition is used in a process in which the composition is coated on the substrate prior to coating of substrate, is contacted with an alkaline aqueous solution after baking, then the photoresist, and photoresist is coated, the composition~~ comprises a polymer having a hydroxy group or a carboxy group and a crosslinking ~~agent~~, agent, and a gap fill material layer manufactured by coating the gap fill material forming composition on a semiconductor substrate and baking it has a dissolution rate for an alkaline aqueous solution having a concentration of 0.1% to 20% ranging from 3 to 200 nm per second.
2. (Original) The gap fill material forming composition according to claim 1, wherein the polymer has a weight average molecular weight of 500 to 30000.
3. (Original) The gap fill material forming composition according to claim 1, wherein the polymer is a polymer containing repeating unit having a hydroxy group or a carboxy group in main chain.
4. (Original) The gap fill material forming composition according to claim 1, wherein the polymer is a polymer containing repeating unit having a hydroxy group or a carboxy group in side chain.
5. (Original) The gap fill material forming composition according to claim 1, wherein the polymer is a polymer containing acrylic acid or methacrylic acid as repeating unit.

6. (Original) The gap fill material forming composition according to claim 1, wherein the polymer is a polymer containing hydroxyalkyl acrylate or hydroxyalkyl methacrylate as repeating unit.

7. (Original) The gap fill material forming composition according to claim 1, wherein the polymer is a dextrin ester compound.

8. (Original) The gap fill material forming composition according to claim 1, wherein the polymer is a polymer containing hydroxystyrene as repeating unit.

9. (Previously Presented) The gap fill material forming composition according to claim 1, wherein the polymer has no aromatic ring structure in the structure.

10. (Original) The gap fill material forming composition according to claim 1, wherein the crosslinking agent is a crosslinking agent having at least two crosslink-forming functional groups.

11. (Previously Presented) The gap fill material forming composition according to claim 1, further containing an alkali-dissolution rate regulator.

12. (Previously Presented) A method for forming a gap fill material layer for use in manufacture of semiconductor device comprising coating the gap fill material forming composition according to claim 1 on a substrate and baking it.

13. (Canceled)